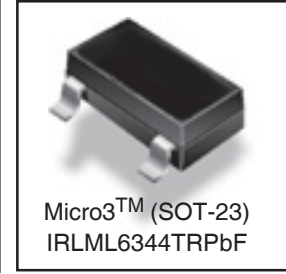
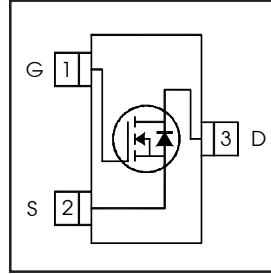


# IRLML6344TRPbF

HEXFET® Power MOSFET

<b>V<sub>DS</sub></b>	<b>30</b>	<b>V</b>
<b>V<sub>GS Max</sub></b>	<b>± 12</b>	<b>V</b>
<b>R<sub>DS(on) max</sub></b> (@ V <sub>GS</sub> = 4.5V)	<b>29</b>	<b>mΩ</b>
<b>R<sub>DS(on) max</sub></b> (@ V <sub>GS</sub> = 2.5V)	<b>37</b>	<b>mΩ</b>



## Application(s)

- Load/ System Switch

## Features and Benefits

Low R <sub>DS(on)</sub> (<29mΩ)
Industry-standard SOT-23 Package
RoHS compliant containing no lead, no bromide and no halogen
MSL1, Consumer Qualification

results in

## Benefits

Lower Conduction Losses
Multi-vendor compatibility
Environmentally friendly
Increased Reliability

## Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
V <sub>DS</sub>	Drain-Source Voltage	30	V
I <sub>D</sub> @ T <sub>A</sub> = 25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	5.0	A
I <sub>D</sub> @ T <sub>A</sub> = 70°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	4.0	
I <sub>DM</sub>	Pulsed Drain Current	25	
P <sub>D</sub> @ T <sub>A</sub> = 25°C	Maximum Power Dissipation	1.3	W
P <sub>D</sub> @ T <sub>A</sub> = 70°C	Maximum Power Dissipation	0.8	
	Linear Derating Factor	0.01	
V <sub>GS</sub>	Gate-to-Source Voltage	± 12	V
T <sub>J</sub> , T <sub>STG</sub>	Junction and Storage Temperature Range	-55 to + 150	°C

## Thermal Resistance

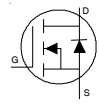
Symbol	Parameter	Typ.	Max.	Units
R <sub>θJA</sub>	Junction-to-Ambient ③	—	100	°C/W
R <sub>θJA</sub>	Junction-to-Ambient (t<10s) ④	—	99	

# IRLML6344TRPbF

## Electric Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	30	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.02	—	V/°C	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	22	29	m $\Omega$	$V_{GS} = 4.5V, I_D = 5.0A$ ②
		—	27	37		$V_{GS} = 2.5V, I_D = 4.0A$ ②
$V_{GS(th)}$	Gate Threshold Voltage	0.5	0.8	1.1	V	$V_{DS} = V_{GS}, I_D = 10\mu A$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	1.0	$\mu A$	$V_{DS} = 24V, V_{GS} = 0V$
		—	—	150		$V_{DS} = 24V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 12V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -12V$
$R_G$	Internal Gate Resistance	—	1.7	—	$\Omega$	
$g_{fs}$	Forward Transconductance	19	—	—	S	$V_{DS} = 10V, I_D = 5.0A$
$Q_g$	Total Gate Charge	—	6.8	—	nC	$I_D = 5.0A$
$Q_{gs}$	Gate-to-Source Charge	—	0.3	—		$V_{DS} = 15V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	2.4	—		$V_{GS} = 4.5V$ ②
$t_{d(on)}$	Turn-On Delay Time	—	4.2	—	ns	$V_{DD} = 15V$ ②
$t_r$	Rise Time	—	5.6	—		$I_D = 1.0A$
$t_{d(off)}$	Turn-Off Delay Time	—	22	—		$R_G = 6.8\Omega$
$t_f$	Fall Time	—	9.1	—		$V_{GS} = 4.5V$
$C_{iss}$	Input Capacitance	—	650	—	pF	$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	—	65	—		$V_{DS} = 25V$
$C_{rss}$	Reverse Transfer Capacitance	—	46	—		$f = 1.0\text{MHz}$

## Source - Drain Ratings and Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	1.3	A	MOSFET symbol showing the integral reverse p-n junction diode. 
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	25		
$V_{SD}$	Diode Forward Voltage	—	—	1.2	V	$T_J = 25^\circ\text{C}, I_S = 5.0A, V_{GS} = 0V$ ②
$t_{rr}$	Reverse Recovery Time	—	10	15	ns	$T_J = 25^\circ\text{C}, V_R = 15V, I_F = 1.3A$
$Q_{rr}$	Reverse Recovery Charge	—	3.8	5.7	nC	$di/dt = 100A/\mu s$ ②